TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K15FU

High Speed Switching Applications Analog Switch Applications

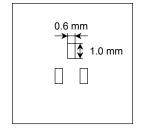
- Small package
- Low on resistance
 - : $R_{on} = 4.0 \Omega (max) (@V_{GS} = 4 V)$
 - : $R_{on} = 7.0 \Omega (max) (@V_{GS} = 2.5 V)$

Maximum Ratings (Ta = 25°C)

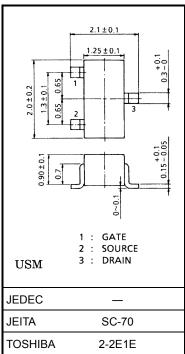
Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DS}	30	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC	I _D	100	mA	
	Pulse	I_{DP}	200		
Drain power dissipation (Ta = 25°C)		P _D (Note)	150	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature		T _{stg}	-55~150	°C	

Note: Mounted on FR4 board

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ t}, \text{ Cu Pad: } 0.6 \text{ mm}^2 \times 3)$



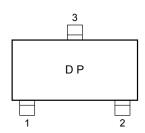
Unit: mm

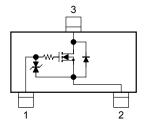


Weight: 0.006 g (typ.)

Marking

Equivalent Circuit





Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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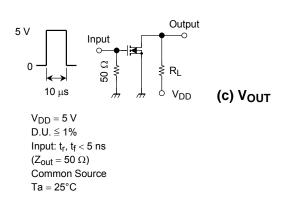
Electrical Characteristics (Ta = 25°C)

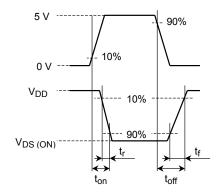
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$	_	_	±1	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 0.1 \text{ mA}, V_{GS} = 0$	30	_	_	V
Drain cut-off curre	nt	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0$	_	_	1	μΑ
Gate threshold vo	Itage	V _{th}	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	8.0	_	1.5	V
Forward transfer a	admittance	Y _{fs}	$V_{DS} = 3 \text{ V}, I_{D} = 10 \text{ mA}$	25	_	_	mS
Drain-source ON resistance		R _{DS} (ON)	$I_D = 10$ mA, $V_{GS} = 4$ V	_	2.2	4.0	Ω
			$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	4.0	7.0	
Input capacitance		C _{iss}	V _{DS} = 3 V, V _{GS} = 0, f = 1 MHz	_	7.8	_	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 3 V$, $V_{GS} = 0$, $f = 1 MHz$	_	3.6	_	pF
Output capacitance		C _{oss}	$V_{DS} = 3 V$, $V_{GS} = 0$, $f = 1 MHz$	_	8.8	_	pF
Switching time	Turn-on time	t _{on}	V _{DD} = 5 V, I _D = 10 mA, V _{GS} = 0~5 V	_	50	_	ns
	Turn-off time	t _{off}		_	180	_	

Switching Time Test Circuit









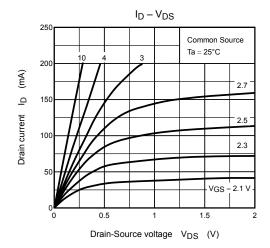
Precaution

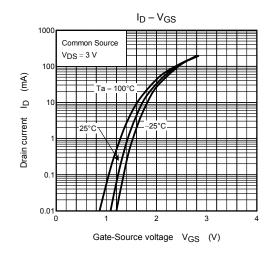
 V_{th} can be expressed as voltage between gate and source when low operating current value is $I_D = 100~\mu A$ for this product. For normal switching operation, V_{GS} (on) requires higher voltage than V_{th} and V_{GS} (off) requires lower voltage than V_{th} .

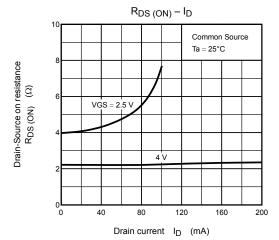
(relationship can be established as follows: $V_{GS\,(off)} < V_{th} < V_{GS\,(on)}$)

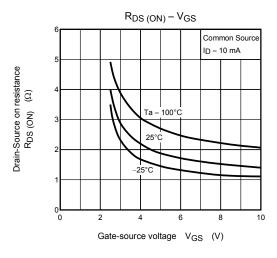
Please take this into consideration for using the device.

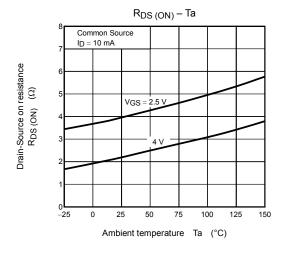
VGS recommended voltage of 2.5 V or higher to turn on this product.

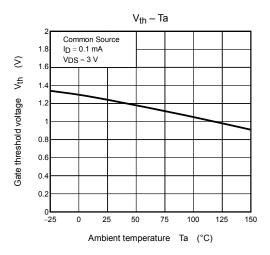




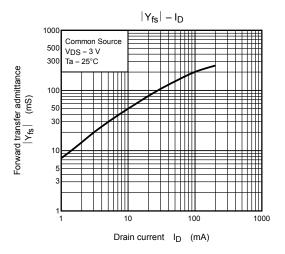


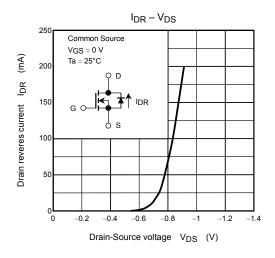


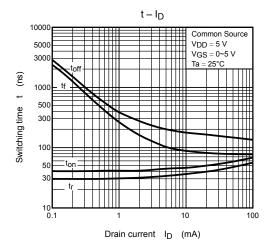


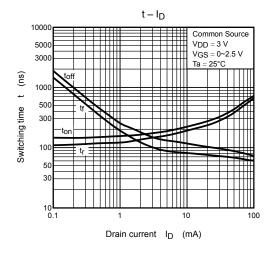


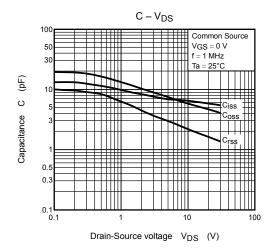
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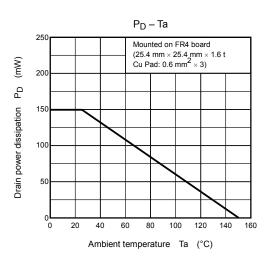












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